THIN FILM LIGHT EMITTING ELEMENT AND MANUFACTURE THEREOF

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Inventor:

ISHIKO MASAYASU

Applicant:

NIPPON ELECTRIC CO

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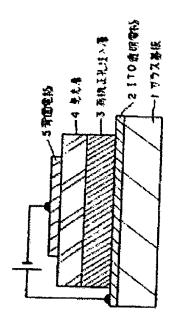
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Abstract of JP2288092

PURPOSE:To multiple luminescent colors, enhance luminous efficiency and reduce deterioration speed by dispersing fluorescent organic molecules into a metal oxide or metal sulfide by a predetermined method so as to form a light emitting layer. CONSTITUTION: A light emitting layer 4 is sandwiched together with an organic normal hole injection layer 3 between a pair of electrodes 2, 5. The light emitting layer 4 made of metal oxide is formed by the method wherein a solution of at least one kind among metal alkoxide, metal acetyl acetonate or metal carboxylate, and a solution of at least more than one kind of fluorescent organic molecule are mixed together and applied to form a film. After the mixture is applied, it is dried in hydrogen sulfide atmosphere so that a light emitting layer 4 made of metal sulfide is formed.



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@発明者 石子 雅泰

東京都港区芝5丁目33番1号 日本電気株式会社内

⑪出 顋 人 日本電気株式会社 東京都港区芝5丁目7番1号

四代 理 人 弁理士 舘野 千恵子

明細盤

1. 発明の名称

薄膜発光素子およびその製造方法

- 2. 特許請求の範囲
- (1) 少なくとも一方が透明である一対の電極間に、 少なくとも1層以上の発光圏を挟持してなる薄膜発光素子において、少なくとも1つの発光圏が、金属酸化物または金属硫化物中に少なくとも1種の蛍光性有機分子を分散させたものであることを特徴とする薄膜発光素子。
- (2) 少なくとも一方が透明である一対の電極間に、 少なくとも1層以上の発光層を挟持してなる 育 膜発光素子の製造方法において、少なくとも1 つの発光層が、金属アルコキシド、金属アセセチ ルアセトネートおよび金属カルボキシレートの うちの少なくとも1種からなる溶液を混合し、 該混合液を基材上に塗布・成膜することに 算 形成されたものであることを特徴とする薄

光素子の製造方法。

3. 発明の詳細な説明

[産桑上の利用分野]

本発明は平面光源やディスプレイに使用される 稗膜発光素子およびその製造方法に関するもので ある。

[従来の技術]

有機物質を原料としたEL(電界発光)素子は、 その豊富な材料数と分子レベルの合成技術で、安 価な大面積フィルム状フルカラー表示素子を実現 するものとして注目を集めている。例えばアント ラセンやベリレン等の縮合多環芳香族系を原料と してLB法や真空蒸替法等で薄膜化した直流駆動 の有機薄膜発光素子が製造され、その発光特性が 研究されている。

更に、最近有機薄膜を2層構造にした新しいタイプの有機薄膜発光素子が報告され、強い関心を集めている(アプライド・フィジックス・レターズ、51巻、 913ページ、1987年参照)。報告によれば、第2図に示すように、強い蛍光を発する金

属キレート化合物を有機蛍光体薄膜圏24に、アミン系材料を正孔伝導性有機物の有機正孔注入圏23に使用して明るい緑色発光を得たことが開示されており、6~7 Vの直流印加で数100 cd/元の輝度が得られている。また、最大発光効率は 1.5 ℓ m/Wと、実用レベルに近い性能を持っている。

【発明が解決しようとする課題】

前述したように、有機蛍光体薄膜層24と有機正孔注入層23が2層積層した構造を有している新しい有機薄膜発光素子は、最大発光輝度が 1000 cd/ エ以上の明るい緑色発光を示す。しかしながら、多色発光する有機薄膜発光素子については、新しいも大力・アプライド・フィジックス、27巻、 し 269頁、1988年参照)や、別の有機で、第4回国際エレクトロルミネセンスので、第4回国際エレクトロルミネセンスのクショップ予箱集、 124ページ、1988年参始の本とが試みられているものの、青色発光を始めなる緑色以外の発光は、輝度レベル、発光効率など

[作用]

有機溶膜発光素子は、夏富な有機材料から高効率発光層あるいは発光中心を選択あるいは合成できるという特徴がある。しかし、従来の発光素子のように、真空蒸着で製造する場合、高真空下で適当な蒸気圧をもつ有機材料は、現時点では多くない。特に、有機材料の蒸気圧を高くすると、その材料のもつ蛍光量子効率が若しく低下すること

の点で満足できるレベルにない。

さらに、従来使用していた有機薄膜発光素子では、電圧印加時間とともに素子の電圧-発光特性の高電圧側移動が顕著であり、低電圧駆動では発光輝度の低下をもたらしていた。これは、有機薄膜光素子を構成する有機薄膜の電気特性の変動が大きいことが原因の1つであった。また、発光輝度の低下を補うために駆動電圧を増加させると、電力損(ジュール熱)も増大し、その結果、発光輝度の劣化速度が更に加速されるという悪循環も観察された。

本発明は、以上述べたような従来の問題点を解決するためになされたもので、発光色の多様化とともに、素子発光効率を更に向上させ、かつ劣化速度を低下させることが可能な薄膜発光素子およびその製造方法を提供することを目的とする。

[課題を解決するための手段]

本発明は、少なくとも一方が透明である一対の 電極間に、少なくとも1層以上の発光層を挟持し てなる薄膜発光素子において、少なくとも1つの

がよく観察された。蛍光量子効率の高い有機分子を使用するほど有機薄膜発光素子の発光効率が高くなるが、従来蒸奢で成膜でき、かつこのような条件を満たす有機材料は少ない。適当な蒸気圧をもつ有機材料で、かつ高い蛍光量子効率を有するという条件を満足する材料を得ることは、素子の多色化・高効率化に最も重要であるが、きわめて困難であった。

また、高電界・高電流駆動という過酷な条件の もとで安定した電気的特性を示す有機材料も現時 点では多くない。

そこで、安定した電気特性を示す無機材料中に 蛍光効率の高い分子を分散させた薄膜発光素子の 開発研究を行った結果、金属酸化物または金属硫 化物中に少なくとも 1 種の蛍光性有機分子を分散 させた蛍光圏が良好な結果を有することを見い出 した。

また、その製造方法は、金属アルコキシドあるいは金属アセチルアセトネートあるいは金属カルボキシレートの少なくとも1種からなる溶液と、

少なくとも1種以上の蛍光性有機分子からなる溶液を混合し、これを塗布して成膜する、いわゆるソルーゲル法によって金属酸化物よりなる有機蛍光体分子添加の発光層を製造することができる。また塗布後の乾燥工程を硫化水素(H2S)雰囲気中で行えば金属硫化物よりなる発光層が得られる。

有機の蛍光性分子を保持する無機材料の選択基準としては、有機蛍光分子の基底および励起レベルが材料のバンドギャップ内であることである。これは、有機蛍光体分子を有効に励起するためである。また、分散させる有機物の特性劣化を防止するためには、成膜プロセス温度は 250℃以でなければならない。上記の材料より得られる金属酸化物あるいは硫化物はこのような条件を満たすことができる。

また、この発明によれば、薄膜発光素子のディスプレイ・デバイス化に不可欠な発光層のレジストエ程が可能である。

さらに、本発明により、各種有機蛍光体分子を

を使用したディップコーティング法で形成した。 充分乾燥させたのち、Si(OC2 H5)4を 1:4の比率で水ーアルコール系の溶液で溶かし た溶媒を作る。この溶媒の中に有機蛍光体として トリス(8ーハイドロキシキノリン)アルミニウ ムを約 40 重量%混合し、充分慢拌する。その後、 ガラス基板をこの溶液に没し、ゆっくり引き上げ て発光層4を形成した。乾燥後の膜厚は約 800人 であった。最後に、MgとAgを10:1で混合し た合金の背面金属電極5を電子ビーム蒸着法で 1500 人形成して薄膜発光素子が完成する。

この素子の発光特性を乾燥窒素中で測定したところ、約8Vの直流電圧の印加で 300 cd / dの緑色の発光が得られた。従来の素子に比べ、発光輝度・効率が2~5倍改善されていることがわかる。この薄膜発光素子を電流密度 0.5 mA / cm² の状態でエージング試験をしたところ、輝度半減時間は 1000 時間以上であった。従来の素子では、100~ 300時間であったから、この素子の信頼性は大幅に改善されている。また、電気特性のシフ

混合し、発光の多色化を図ることが容易にできるようになる。即ち、従来、素子は真空蒸着法でである。即ち、従来では成題難であったが、この方法では成敗強い有機となり、この結果、強い育色発アルシーのが可能となり、この結果、強い何色はアルシーを発明では、例えばアルミシー・ナノリノール錯体に対して10⁻³ ■01のローダミ圏・ナノリノール錯体に対して成膜した発光を得ることができる。そのなりは、正確に再現性よく、簡単に制御できる。
【実施例】

次に本発明の実施例について詳細に説明する。 _{電船} M 1

第1図は本発明の一実施例により得られた薄膜発光素子の断面図である。同図に示すように、ガラス基板1上にITO透明電板2を形成してからポリ(メチルフェニルシリレン)約 60 重量%にN,N,N',N'-テトラフェニルー4.4'ージアミノビフェニルを約 40 重量%混合したポリシリレンからなる有機正孔注入層3を 1500 人、トルエン溶媒

トも5 V程度と、従来より大幅に低下した。

本実施例ではトリス(8-ハイドロキシキノリン)アルミニウム有機蛍光体を用いたが、アントラセン・ピレン・テトラセン・スチルベン・パリレン・キノン・フェナンスレン・ナフタレン誘導体等、他の有機蛍光体に10-5~10-2 mol 程度のローダミン・シアニン・ピラン・クマリン・フルオレン・POPOP等、他の蛍光の強い有機分子を更に添加して、各種の発光色を得ることができる。透明電極はITO以外にZnO:AℓやSnO2 :Sb.Auなどでもよい。

実施例2

 TiO_2 、ZnO、 VO_X の膜をゾルーゲル法で製造する際に、トリス(8-ハイドロキシキノリン)アルミニウムを添加して、実施例1における発光魔4を成膜しても、優れた薄膜発光素子を形成できた。表-1は、成膜に使用した材料を示したものである。

表-1

T i O ₂	Ti (OCH ₃) ₄
	Ti (OC2 H5)4
	Ti (O-i-C3 H7)4
	Ti (O-n-C3 H7)4
	Ti (O-n-C4 H9)4
	Ti (O-i-C4 H9)4
	Ti (O-sec-C4 H9)4
	Ti (0-t-C4 H9)4
ZnO	Zn (OC2 H5)2
	Zn (OCH ₃) ₂
	Zn (O-n-C3 H7)2
	Zn (O-n-C4 H9)2
VO _x	VO (OCI13) 3
	VO (O-i-C ₃ H ₇) ₃
	VO (O-n-C ₃ H ₇) ₃
	VO (0-i-C4 H9)3
	VO (0-n-C4 H9)3
	VO (O-sec-C ₄ H ₉) ₃
	vo (o−t-C₄ H ₉) 3

ITO透明電極2かついたガラス基板1上に無金属フタロシアニンを200人蒸発して有機正孔注入層3とする。その後、このガラス基板を実施例3で用いた亜鉛アセチルアセトネート溶液に浸砂し、150℃、硫化水素(H2S)雰囲気中で乾燥する。そうすると、発光層4の一部が硫化物となると共に、発光開始電圧の低下が認められた。また光層4を乾燥させる過程でH2Sを使用し、発光層を硫化しても優れた薄膜発光素子が製造できた。

以上のように、本発明で重要な点は、少なくとも1つの透明な発光層が金属アルコキシドあるいは金属アセチルアセトネートあるいは金属カルボキシレートの中の少なくとも1種からなる溶液と 蛍光性有機分子からなる溶液を混合し、塗布して成膜したことを特徴とした薄膜発光素子の製造方法であり、素子を構成する材料そのものを限定するものではない。

[発明の効果]

以上説明したように、本発明によれば発光特性

なおTiO2 、2 n O 、V O x およびS i O x を適当に混合し、これにアントラセン、ピレン・テトラセン、スチルベン・ペリレン・キノン、フェナンスレン・ナフタレン誘導体等の有機分子を添加して成膜してなる発光圏 4 を使用しても優れた
沈加する有機分子としてクマリンやフルオレンの 誘導体等が使用できた。

実施例3

実施例1におけるSi(OC2 Hs)4 の溶 被のかわりに亜鉛アセチルアセトネート(2 n (COCH2 COCH3)2)を含む溶液を用い た以外は実施例1と同様にして発光圏4を成膜し ても優れた神膜発光素子を形成することができ た。

また、その他のアセチルアセトネートやCu (CH3 COO)2 のような物質を使用して発光 腐4を形成しても優れた薄膜発光素子を製造する ことができた。

実施例4

および信頼性が大幅に改善された多色発光の薄膜 発光素子およびその製造方法が提供される。

本発明により得られる効果を詳述すると、

- ① 背色を始め、多色発光する神膜発光素子が提供 される。
- ②従来、真空蒸替法で製造困難であった蛍光効率の高い有機分子(例えばアントラセン)の添加が可能となり、素子発光効率が向上した。その結果、発光効率の低さに起因する発熱や、熱による素子特性劣化の加速などを低下させることが可能となった。
- ③レジスト工程を可能とし、ディスプレイ化が容易になった。

このように、本発明により実用レベルの低電圧 直流駆動薄膜発光素子とその製造方法を提供でき、 その工業的価値は高い。

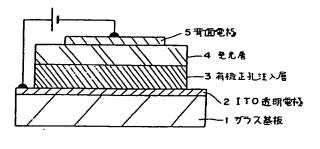
4. 図面の簡単な説明

第1図は本発明の一実施例により得られた薄膜 発光素子の断面図、第2図は従来の有機薄膜発光 素子の断面図である。

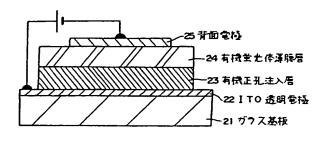
特別平2-288092 (5)

- 1,21…ガラス基仮
- 2. 22··· I T O 透明電極
- 3.23…有機正孔注入層
- 4 … 発光層
- 5.25…背面電極
- 24…有機蛍光体薄膜圈

代理人 弁理士 舘 野 千 惠 子



第1図



第 2 図

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 - (71) Applicant: NIPPON ELECTRIC CO., LTD
- 15 5-7-1 Shiba, Minato-ku, Tokyo
 - (72) Inventor: Masayasu ISHIKO

c/o NIPPON ELECTRIC CO., LTD

5-33-1 Shiba, Minato-ku, Tokyo

(74) Representative: Patent attorney

20 Chieko TATENO

Specification

1. Title of the Invention

THIN FILM LIGHT-EMITTING ELEMENT AND MANUFACTURING METHOD
THEREOF

2. Scope of Claim

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- (1) A thin film light-emitting element characterized by comprising at least one or more light-emitting layer interposed between a pair of electrodes at least either of which is transparent, wherein at least one light-emitting layer is one in which at least one kind of fluorescent organic molecule is dispersed into metal oxide or metal sulfide.
- (2) A manufacturing method of a thin film light-emitting element including at least one or more light-emitting layer interposed between a pair of electrodes at least either of which is transparent, characterized in that at least one light-emitting layer is formed by mixing a solution containing at least one kind of metal alkoxide, metal acetylacetonate, or metal carboxylate with a solution containing at least one kind of fluorescence organic molecule, and then applying the mixed solution on a substrate to form a film.
- 3. Detailed Description of the invention

[Industrial Field of the Invention]

The present invention relates to a thin film light-emitting element used for a planar light source and a display, and a manufacturing method thereof.

[Related Art]

An EL (electroluminescent) element a material of which is an organic substance has attracted attention as an element for realizing an inexpensive, large area, and film-like full color display element due to an ample number of materials and a synthesis technique at molecular level. For example, a condensed polycyclic aromatic compound based material such as anthracene or perylene is used for manufacturing a direct current organic thin film light-emitting element which is thinned by an LB method, a vacuum vapor deposition method, or the like and the light emitting characteristic has been studied.

Further, a new type organic thin film light-emitting element which has

two-layered structure in the organic thin film has been reported, which has attracted a keen interest (see Applied Physics Letters, volume 51, p. 913, 1987). According to the report, as shown in FIG. 2, it is disclosed that a metal chelate compound which strongly fluoresces is used for an organic fluorescence thin film layer 24 and an amine based material is used for an organic hole injection layer 23 which is a hole conductive organic material, thereby bright green light emission is obtained. Luminance of several 100 cd/m² has been obtained by direct current application of 6~7 V. Moreover, the maximum luminance efficiency is 1.5 lm/W, which is a performance close to a practical level.

[Problems to be solved by the invention]

As previously mentioned, the new organic thin film light-emitting element in which the two-stacked layer of the organic fluorescence thin film layer 24 and the organic hole injection layer 23 shows bright green emission of 1000 cd/m² or more at a maximum light emission luminance. However, concerning an organic thin film light-emitting element which emits multicolor, development of a new organic fluorescence thin film (see Japanese Journal of Applied Physics, volume 27, L p.269, 1988), addition of other organic coloring matters (see Proceedings of the Fourth International Electroluminescence Workshop, p.124, 1988), or the like has been attempted, light emission other than green, including blue light emission is not on satisfaction level in terms of luminance level, light-emitting efficiency, and the like.

Further, in an organic thin film light-emitting element which has been conventionally used, as the time of voltage application gets longer a voltage-light emission characteristic of the element markedly shifts to a high-voltage side so that light emission luminance has reduced in low voltage driving. This partly resulted from large variation in electrical characteristics of an organic thin film which formed the organic thin film light-emitting element. In addition, vicious circle was observed that when a driving voltage was increased to compensate for reduction in light emission luminance, electric power loss (joule heat) was increased, and accordingly, deterioration rate of light emission luminance was further accelerated.

The present invention is aimed at solving the conventional problems mentioned

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above. An object of the present invention is to provide a thin film light-emitting element which further improves light-emitting efficiency of an element and reduces deterioration rate together with diversification in emission color, and a manufacturing method thereof.

5 [Means for Solving the Problem]

The present invention is directed to a thin film light-emitting element characterized by comprising at least one light-emitting layer interposed between a pair of electrodes at least either of which is transparent, wherein at least one or more light-emitting layer is one in which at least one kind of fluorescent organic molecule is dispersed into metal oxide or metal sulfide. Moreover, a manufacturing method of the thin film light-emitting element including at least one light-emitting layer interposed between a pair of electrodes at least either of which is transparent characterized in that at least one light-emitting layer is formed by mixing a solution containing at least one kind of metal alkoxide, metal acetylacetonate, or metal carboxylate with a solution containing at least one kind of fluorescence organic molecule, and then applying the mixed solution on a substrate to form a film.

[Operation]

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The organic thin film light-emitting element has a characteristic such that a highly efficient light-emitting layer or a light-emitting center can be selected or synthesized from a wide range of organic materials. However, in a case where vacuum vapor deposition as in a conventional light-emitting element manufacture is employed, there are not many organic materials having a suitable steam pressure under high vacuum at the present time. In particular, when steam pressures in organic materials were made high, marked reduction in fluorescence quantum efficiency of the materials was often observed. The higher fluorescence quantum efficiency of organic molecules are used, the higher light-emitting efficiency of organic thin film light-emitting elements becomes, however there are a few organic materials which can be formed by conventional deposition and satisfy such conditions. It has been extremely difficult to obtain materials which satisfy condition such that materials are organic materials having suitable steam pressures and high fluorescence quantum efficiency, while it is most

significant in order to realize multicolor and highly efficiency of elements.

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Furthermore, there are a few organic materials, at the present time, showing a stable electrical characteristic under serious conditions of high electric field and high current driving.

From the results of development research on thin film light-emitting elements in which molecules having high fluorescence efficiency are dispersed into inorganic materials showing a stable electrical characteristic, it was found that fluorescence layers in which at least one kind of fluorescence organic molecule is dispersed into metal oxide or metal sulfide attain good results.

A light emitting-layer formed of metal oxide to which organic fluorescence molecules are added can be manufactured by so-called sol-gel processing in which a solution containing at least one kind of metal alkoxide, metal acetylacetonate, or metal carboxylate is mixed with a solution containing at least one or more kind of fluorescence organic molecule, and then applied to form a film. In addition, when a drying process after application is performed under a hydrogen sulfide (H₂S) atmosphere, a light-emitting layer formed of metal sulfide can be obtained.

The selecting standard of inorganic materials which hold fluorescence organic molecules is that ground and excitation levels of fluorescence organic molecules are within band gaps of the materials. This is because in order to effectively excite fluorescence organic molecules. Further, to prevent deterioration in property of organic materials which are dispersed, a temperature of film formation process should be equal to or lower than 250 °C. Metal oxide or metal sulfide which is obtained from the above materials can satisfy these conditions.

According to this invention, a resist process for light emitting layers which is essential for manufacturing display devices with use of thin film light-emitting elements can be performed.

Furthermore, the present invention makes it possible to easily mix various fluorescence organic molecules and to easily design multicolor emission. That is, organic materials which strongly fluoresce such as anthracene or pylene which are difficult to be formed into films by vacuum vapor deposition conventionally used to

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manufacture elements can be added, thereby strong blue light-emitting element is realized. Moreover, in the present invention, for example, red light emission can be obtained by using a light-emitting layer formed by adding a solvent in which rhodamine 6G of 10⁻³ mol is mixed with aluminum quinolinol complex. The additive amount can be easily controlled with accurate reproductivity.

[Embodiment]

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Next, embodiments of the present invention will be described in details. Embodiment 1

FIG. 1 is a cross-sectional view of the thin film light-emitting element obtained from an embodiment of the present invention. As shown in the figure, an ITO transparent electrode 2 was formed on a glass substrate 1, and then an organic hole injection layer 3 formed of polysilylene in which approximately 40 wt. % of N,N,N',N'-tetraphenyl-4,4'-diaminolbiphenyl is mixed into approximately 60 wt. % of poly (methylphenylsilylene) was formed with 1500 Å by a dip coating method using a toluene solvent. After the organic hole injection layer 3 was sufficiently dried, a solvent in which Si (OC₂H₅)₄ was dissolved into a water-alcohol based solution with a ratio of 1 to 4 was made. Into this solvent, approximately 40 wt. % of tris(8-hydroxyquinoline)aluminum was mixed as an organic fluorescence and sufficiently stirred. After that, the glass substrate was dipped into this solution and slowly pulled up so that a light-emitting layer 4 could be formed. The film thickness after dry was approximately 800 Å. Finally, a back metal electrode 5 which is an alloy of Mg and Ag mixed with a ratio of 10 to 1 was formed with 1500 Å by electron beam deposition. Thus, the thin film light-emitting element was completed.

When a light-emitting characteristic of this element was measured under dry nitrogen, green light emission of 300 cd/m² could be obtained by application of approximately 8 V direct current. Compared to the conventional element, it was found that light emission luminance and efficiency was improved 2~5 times. When an aging experiment was performed on this thin film light-emitting element with a current density of 0.5 mA/cm², time to half luminance was more than 1000 hours. Since in the conventional element, time to half luminance was 100~300 hours, this element has

considerably improved reliability. A shift in an electrical characteristic was approximately 5V, which has more considerably reduced than that of the conventional ones.

Although in this embodiment tris(8-hydroxyquinoline)aluminum organic fluorescence was used, similar effect was observed using other organic materials such as anthracene, pyrene, tetracene, stilbene, perylene, quinone, phenanthrene, or naphthalene derivative. Moreover, other organic molecules of approximately $10^{-5} \sim 10^{-2}$ mol, which strongly fluoresce, such as rhodamine, cyanine, pyran, coumarin, fluorene, or POPOP can be added into this organic fluorescence, and various light emission colors can be obtained. A transparent electrode may be ZnO:Al, SnO₂:Sb, Au, or the like besides ITO.

Embodiment 2

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In manufacturing a film of TiO₂, ZnO, and VO_x by sol-gel processing, adding tris(8-hydroxyquinoline)aluminum to form the light-emitting layer 4 in Embodiment 1 allows formation of an excellent thin film light-emitting element. Table 1 shows materials used in film formation.

Table-1

	Ti(OCH ₃) ₄
	Ti(OC ₂ H ₅) ₄
	Ti(O-i-C ₃ H ₇) ₄
TiO ₂	Ti(O-n-C ₃ H ₇) ₄
	Ti(O-n-C ₄ H ₉) ₄
	Ti(O-i-C ₄ H ₉) ₄
	Ti(O-sec-C ₄ H ₉) ₄
	Ti(O-t-C ₄ H ₉) ₄
	Zn(OC ₂ H ₅) ₂
ZnO	Zn(OCH ₃) ₂
	$Zn(O-n-C_3H_7)_2$
	$Zn(O-n-C_4H_9)_2$

	VO(OCH ₃) ₃
	VO(O-i-C ₃ H ₇) ₃
	VO(O-n-C ₃ H ₇) ₃
VO _x	VO(O-i-C ₄ H ₉) ₃
	VO(O-n-C ₄ H ₉) ₃
	VO(O-sec-C ₄ H ₉) ₃
	VO(O-t-C ₄ H ₉) ₃

Note that in a case of using the light-emitting layer 4 which is formed such that TiO₂, ZnO, VO_x, and SiO_x are mixed as appropriate, and organic molecules such as anthracene, pyrene, tetracene, stilbene, perylene, quinone, phenanthrene, or naphthalene derivative are added thereto, an excellent thin film light-emitting element could be obtained. In addition, as further additional organic molecules, derivatives such as coumarin or fluorine could be used.

Embodiment 3

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Even though the light-emitting layer 4 was formed as in Embodiment 1 except using a solution containing zinc acetylacetonato (Zn(COCH₂COCH₃)₂ instead of a solution of Si(OC₂H₅)₄ in Embodiment 1, an excellent thin film light-emitting element could be formed.

Moreover, even though the light-emitting layer 4 was formed such that other substances such as acetylacetonato or Cu(CH₃COO)₂ were used, an excellent thin film light-emitting element could be manufactured.

Embodiment 4

The organic hole injection layer 3 was formed such that metal-free phthalocyanine was deposited with 200 Å over the glass substrate 1 to which an ITO transparent electrode 2 was attached. After that, this glass substrate was dipped into a solution containing zinc acetylacetonato which was used in Embodiment 3, and dried under an atmosphere of hydrogen sulfide (H₂S) at 150 °C. This recognizes reduction in a threshold voltage for emission as well as part of the light-emitting layer 4 turned into a hydrogen sulfide and also recognizes improvement in light emission luminance. In this way, even though H₂S was used and the light-emitting layer was sulfide during a

process for drying the light-emitting layer 4, an excellent thin film light-emitting element could be manufactured.

In the foregoing manner, an important point of the present invention is that a manufacturing method of a thin film light-emitting element characterized in that at least one transparent light-transmitting layer is formed by mixing a solution containing at least one kind of metal alkoxide, metal acetylacetonato, or metal carboxylate with a solution containing fluorescence organic molecules, and applying it to form a film. Materials which construct elements themselves are not limited.

[Effect of the Invention]

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As described above, according to the present invention, a thin film light-emitting element emitting multicolor light which is considerably improved in a light emission characteristic and reliability, and a manufacturing method thereof are provided.

Effects obtained from the present invention are described in details as follows;

- ① A thin film light-emitting element which emits multicolor light including blue is provided.
 - ② Organic molecules having high fluorescence efficiency (for example, anthracene) which has been conventionally difficult to manufactured by vacuum vapor deposition can be added. Thereby element light-emitting efficiency has been improved. As a result, heat resulting from low light-emitting efficiency, and accelerated deterioration in element characteristic resulting from the heat can be reduced.
 - 3 A resist process is possible, thus a display can be easily made.

In this way, the present invention makes it possible to provide a light-emitting element with low voltage direct current driving of a practical level, and a manufacturing method thereof. The present invention is of high industrial value.

4. Brief Description of the Drawings

FIG. 1 is a cross-sectional view of the thin film light-emitting element obtained from an embodiment of the present invention, and FIG. 2 is a cross-sectional view of the conventional organic thin film light-emitting element.

30 1, 21 ··· glass substrate

- 2, 22···ITO transparent electrode
- 3, 23 ··· organic hole injection layer
- 4···light-emitting layer
- 5, 25 ··· back electrode
- 5 24 ··· organic fluorescence thin film layer

Representative: Chieko TATENO (patent attorney)